

WHAT IS CLAIMED IS:

1. A semiconductor device comprising:

a first electrode;

an insulating film formed on said first electrode;

a contact hole which is provided in said insulating film and has a depth so as to reach said first electrode;

a gate wiring which is formed on said insulating film and connected with said first electrode through said contact hole;

a second electrode provided on said insulating film; and

a liquid crystal layer provided over said second electrode,

wherein said second electrode is provided so as to block an electric field by said first electrode to said liquid crystal layer.

2. A semiconductor device according to any one of claims 1, wherein a pixel electrode is formed on said insulating film and said second electrode is in contact with said pixel electrode.

3. A semiconductor device according to any one of claims 1, wherein said second electrode is a pixel electrode.

4. A semiconductor device according to claim 1, wherein said semiconductor device is incorporated into an electronic equipment selected from the group consisting of a personal computer, a video camera, a mobile computer, a goggle type display, a player, a digital

camera, a front-type projector, a rear-type projector, a portable telephone, a portable book,  
and a display.

5. A semiconductor device comprising:

5 a semiconductor film;

a gate insulating film provided on said semiconductor film;

a first electrode which is provided on said gate insulating film and overlaps said  
semiconductor film;

an insulating film formed on said first electrode;

10 a contact hole which is provided in said insulating film and has a depth so as to reach  
said first electrode;

a gate wiring which is formed on said insulating film and connected with said first  
electrode through said contact hole;

a second electrode provided on said insulating film; and

15 a liquid crystal layer provided over said second electrode,

wherein said second electrode is provided so as to block an electric field by said first  
electrode to said liquid crystal layer.

6. A semiconductor device according to any one of claims 5, wherein a pixel electrode  
20 is formed on said insulating film and said second electrode is in contact with said pixel  
electrode.

7. A semiconductor device according to any one of claims 5, wherein said second  
electrode is a pixel electrode.

8. A semiconductor device according to claim 5, wherein said semiconductor device is incorporated into an electronic equipment selected from the group consisting of a personal computer, a video camera, a mobile computer, a goggle type display, a player, a digital camera, a front-type projector, a rear-type projector, a portable telephone, a portable book,  
5 and a display.

9. A semiconductor device comprising:  
a first semiconductor film;  
a second semiconductor film;  
10 a gate insulating film provided on said first semiconductor film and said second semiconductor film;  
a first electrode which is provided on said gate insulating film, intersects said first semiconductor film, and overlaps said second semiconductor film;  
an insulating film formed on said first electrode;  
15 a contact hole which is provided in said insulating film and has a depth so as to reach said first electrode;  
a gate wiring which is formed on said insulating film and connected with said first electrode through said contact hole;  
a second electrode provided on said insulating film; and  
20 a liquid crystal layer provided over said second electrode,  
wherein said second electrode is provided so as to block an electric field by said first electrode to said liquid crystal layer.

10. A semiconductor device according to any one of claims 9, wherein a pixel

electrode is formed on said insulating film and said second electrode is in contact with said pixel electrode.

11. A semiconductor device according to any one of claims 9, wherein said second  
5 electrode is a pixel electrode.

12. A semiconductor device according to claim 9, wherein said semiconductor device  
is incorporated into an electronic equipment selected from the group consisting of a personal  
computer, a video camera, a mobile computer, a goggle type display, a player, a digital  
camera, a front-type projector, a rear-type projector, a portable telephone, a portable book,  
and a display.

13. A semiconductor device comprising:  
a first electrode;  
an insulating film formed on said first electrode;  
a contact hole which is provided in said insulating film and has a depth so as to reach  
said first electrode;  
a gate wiring which is formed on said insulating film and connected with said first  
electrode through said contact hole; and  
20 a second electrode provided on said insulating film,  
wherein said first electrode is overlapped at 70 % or more of an area thereof with said  
second electrode.

14. A semiconductor device according to any one of claims 13, further comprising a

liquid crystal layer provided over said second electrode.

15. A semiconductor device according to any one of claims 13, wherein a pixel  
electrode is formed on said insulating film and said second electrode is in contact with said  
5 pixel electrode.

16. A semiconductor device according to any one of claims 13, wherein said second  
electrode is a pixel electrode.

10 17 A semiconductor device according to claim 13, wherein said semiconductor device  
is incorporated into an electronic equipment selected from the group consisting of a personal  
computer, a video camera, a mobile computer, a goggle type display, a player, a digital  
camera, a front-type projector, a rear-type projector, a portable telephone, a portable book,  
and a display.

15 18 A semiconductor device comprising:  
a semiconductor film;  
a gate insulating film provided on said semiconductor film;  
a first electrode which is provided on said gate insulating film and overlaps said  
20 semiconductor film;  
an insulating film formed on said first electrode;  
a contact hole which is provided in said insulating film and has a depth so as to reach  
said first electrode;  
a gate wiring which is formed on said insulating film and connected with said first

electrode through said contact hole; and

a second electrode provided on said insulating film,

wherein a storage capacitor is constructed by said first electrode, said gate insulating film, and said semiconductor film and overlapped at 90 % or more of an area thereof with said  
5 second electrode.

19. semiconductor device according to any one of claims 18, further comprising a liquid crystal layer provided over said second electrode.

20A semiconductor device according to any one of claims 18, wherein a pixel electrode is formed on said insulating film and said second electrode is in contact with said pixel electrode.

21A semiconductor device according to any one of claims 18, wherein said second electrode is a pixel electrode.

22. semiconductor device according to claim 18, wherein said semiconductor device is incorporated into an electronic equipment selected from the group consisting of a personal computer, a video camera, a mobile computer, a goggle type display, a player, a digital  
20 camera, a front-type projector, a rear-type projector, a portable telephone, a portable book, and a display.

23. semiconductor device comprising:

a first semiconductor film;

a second semiconductor film;

a gate insulating film provided on said first semiconductor film and said second semiconductor film;

a first electrode which is provided on said gate insulating film, intersects said first semiconductor film, and overlaps said second semiconductor film;

an insulating film formed on said first electrode;

a contact hole which is provided in said insulating film and has a depth so as to reach said first electrode;

a gate wiring which is formed on said insulating film and connected with said first electrode through said contact hole; and

a second electrode provided on said insulating film,

wherein a storage capacitor is constructed by said first electrode, said gate insulating film, and said second semiconductor film and overlapped at 90 % or more of an area thereof with said second electrode.

24. A semiconductor device according to any one of claims 23, further comprising a liquid crystal layer provided over said second electrode.

25. A semiconductor device according to any one of claims 23, wherein a pixel electrode is formed on said insulating film and said second electrode is in contact with said pixel electrode.

26. A semiconductor device according to any one of claims 23, wherein said second electrode is a pixel electrode.

